

IN THE SPECIFICATION

Please amend the paragraph beginning at page 2, line 4 of the specification as follows:

Referring to Fig. 2, a gate pattern 16 is formed on the active region 14, and source/drain regions 18 are formed in the active region neighboring the gate ~~electrode-pattern~~ 16. Sidewall spacers 20 are formed on sidewalls of the gate ~~electrode-pattern~~ 16. Continuously, a conventional salicide process is applied to the resultant structure to form a silicide layer 22 on the source/drain regions 18 and the gate pattern 16. Because a dent D exists on a boundary between the active region 14 and the isolation layer 12, the silicide layer 22 is formed along a topology of the dent because the silicide layer provided by the salicide process is thin and uniform. Therefore, the silicide layer 22 forms a deep spike 26 to a bottom of the substrate in the dent D. As a result, leakage current occurs due to a focusing of electrical field through the spike 26, making the resulting shallow source/drain structure ineffective for preventing short channel effects such as punch through.